

# AFGHL40T65SPD

## Field Stop Trench IGBT

### 40 A, 650 V

#### Description

Using the novel field stop 3<sup>rd</sup> generation IGBT technology, AFGHL40T65SPD offers the optimum performance with both low conduction loss and switching loss for a high efficiency operation in various applications, which provides 50 V higher blocking voltage and rugged high current switching reliability.

Meanwhile, this part also offers an advantage of outstanding performance in parallel operation.

#### Features

- AEC-Q101 Qualified
- Low Saturation Voltage:  $V_{CE(Sat)} = 1.85\text{ V (Typ.) @ }I_C = 40\text{ A}$
- 100% Of The Part Are Dynamically Tested (Note 1)
- Short Circuit Ruggedness  $> 5\ \mu\text{S @ }25^\circ\text{C}$
- Maximum Junction Temperature:  $T_J = 175^\circ\text{C}$
- Fast Switching
- Tight Parameter Distribution
- Positive Temperature Co-efficient for Easy Parallel Operating
- Co-Packed With Soft And Fast Recovery Diode

#### Typical Applications

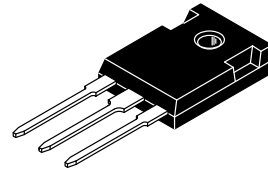
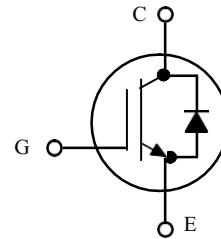
- Onboard Charger
- Air Conditioner Compressor
- PTC Heater
- Motor Drivers
- Other Automotive Power-Train Applications



ON Semiconductor®

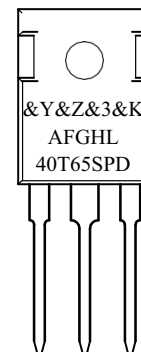
[www.onsemi.com](http://www.onsemi.com)

$V_{CES}$	$E_{on}$	$V_{CE(Sat)}$
650 V	1.16 mJ	1.85 V



TO-247-3L  
CASE 340CX

#### MARKING DIAGRAM



\$Y = ON Semiconductor Logo  
&Z = Assembly Plant Code  
&3 = 3-Digit Data code  
&K = 2-Digit Lot Traceability code  
AFGHL40T65SPD = Specific Device Code

#### ORDERING INFORMATION

Device	Package	Shipping
AFGHL40T65SPD	TO-247-3L	30 Units / Rail

# AFGHL40T65SPD

## ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25°C, Unless otherwise noted)

Symbol	Description	Ratings	Units
V <sub>CES</sub>	Collector to Emitter Voltage	650	V
V <sub>GES</sub>	Gate to Emitter Voltage	±20	V
	Transient Gate to Emitter Voltage	±30	V
I <sub>C</sub>	Collector Current @ T <sub>C</sub> = 25°C	80	A
	Collector Current @ T <sub>C</sub> = 100°C	40	
I <sub>CM</sub>	Pulsed Collector Current (Note 2)	120	A
I <sub>F</sub>	Diode Forward Current @ T <sub>C</sub> = 25°C	40	A
	Diode Forward Current @ T <sub>C</sub> = 100°C	20	
I <sub>FM</sub>	Pulsed Diode Maximum Forward Current (Note 2)	120	A
P <sub>D</sub>	Maximum Power Dissipation @ T <sub>C</sub> = 25°C	267	W
	Maximum Power Dissipation @ T <sub>C</sub> = 100°C	134	
SCWT	Short Circuit Withstand Time @ T <sub>C</sub> = 25°C	5	μs
T <sub>J</sub>	Operating Junction Temperature	-55 to +175	°C
T <sub>stg</sub>	Storage Temperature Range	-55 to +175	°C
T <sub>L</sub>	Maximum Lead Temp. For soldering Purposes, 1/8" from case for 5 seconds	300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. V<sub>CC</sub> = 400 V, V<sub>GE</sub> = 15 V, I<sub>C</sub> = 120 A, R<sub>G</sub> = 20 Ω, Inductive Load
2. Repetitive rating: pulse width limited by max. Junction temperature

## THERMAL CHARACTERISTICS

Symbol	Rating	Max.	Units
R <sub>θJC</sub>	Thermal Resistance junction to case, for IGBT	0.31	°C/W
R <sub>θJC</sub>	Thermal Resistance junction to case, for Diode	1.19	°C/W
R <sub>θJA</sub>	Thermal Resistance junction to Ambient	40	°C/W

# AFGHL40T65SPD

## ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
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### OFF CHARACTERISTICS

Collector-emitter breakdown voltage, gate-emitter short-circuited	V <sub>GE</sub> = 0 V, I <sub>C</sub> = 1 mA	BV <sub>CES</sub>	650	-	-	V
Temperature Coefficient of Breakdown Voltage	V <sub>GE</sub> = 0 V, I <sub>C</sub> = 1 mA		-	0.6	-	V/°C
Collector-emitter cut-off current, gate-emitter short-circuited	V <sub>GE</sub> = 0 V, V <sub>CE</sub> = 650 V V <sub>GE</sub> = 0 V, V <sub>CE</sub> = 650 V, T <sub>J</sub> = 175°C	I <sub>CES</sub>	-	-	250	μA
Gate leakage current, collector-emitter short-circuited	V <sub>GE</sub> = 20 V, V <sub>CE</sub> = 0 V	I <sub>GES</sub>	-	-	±400	nA

### ON CHARACTERISTICS

Gate-emitter threshold voltage	V <sub>GE</sub> = V <sub>CE</sub> , I <sub>C</sub> = 40 mA	V <sub>GE(th)</sub>	4.0	5.0	7.5	V
Collector-emitter saturation voltage	V <sub>GE</sub> = 15 V, I <sub>C</sub> = 40 A V <sub>GE</sub> = 15 V, I <sub>C</sub> = 40 A, T <sub>J</sub> = 175°C	V <sub>CE(sat)</sub>	1.4	1.85	2.4	V
			-	2.51	-	

### DYNAMIC CHARACTERISTICS

Input capacitance	V <sub>CE</sub> = 30 V, V <sub>GE</sub> = 0 V, f = 1 MHz	C <sub>ies</sub>	-	1518	-	pF
Output capacitance		C <sub>oes</sub>	-	91	-	
Reverse transfer capacitance		C <sub>res</sub>	-	15	-	
Gate charge total	V <sub>CE</sub> = 400 V, I <sub>C</sub> = 40 V, V <sub>GE</sub> = 15 V	Q <sub>g</sub>	-	36	-	nC
Gate to emitter charge		Q <sub>ge</sub>	-	11	-	
Gate to collector charge		Q <sub>gc</sub>	-	12	-	

### SWITCHING CHARACTERISTICS

Turn-on delay time	T <sub>C</sub> = 25°C V <sub>CC</sub> = 400 V, I <sub>C</sub> = 40 A R <sub>g</sub> = 6 Ω V <sub>GE</sub> = 15 V Inductive Load, T <sub>C</sub> = 25°C	td(on)	-	18	-	ns	
Rise time		t <sub>r</sub>	-	42	-		
Turn-off delay time		td(off)	-	35	-		
Fall time		t <sub>f</sub>	-	10	-		
Turn-on switching loss		E <sub>on</sub>	-	1.16	-	mJ	
Turn-off switching loss			E <sub>off</sub>	-	0.27		-
Total switching loss			E <sub>ts</sub>	-	1.43		-
Turn-on delay time	T <sub>C</sub> = 175°C V <sub>CC</sub> = 400 V, I <sub>C</sub> = 40 A R <sub>g</sub> = 6 Ω V <sub>GE</sub> = 15 V Inductive Load	td(on)	-	16	-	ns	
Rise time		t <sub>r</sub>	-	40	-		
Turn-off delay time		td(off)	-	37	-		
Fall time		t <sub>f</sub>	-	11	-		
Turn-on switching loss		E <sub>on</sub>	-	1.59	-	mJ	
Turn-off switching loss			E <sub>off</sub>	-	0.42		-
Total switching loss			E <sub>ts</sub>	-	2.01		-

### DIODE CHARACTERISTICS

Forward voltage	I <sub>F</sub> = 20 A I <sub>F</sub> = 20 A, T <sub>J</sub> = 175°C	V <sub>F</sub>	1.4	2.2	2.7	V
Reverse Recovery Time	T <sub>J</sub> = 25°C	t <sub>rr</sub>	-	35	-	ns
Reverse Recovery Charge	I <sub>F</sub> = 20 A, di <sub>F</sub> /dt = 200 A/μs	Q <sub>rr</sub>	-	58	-	μC

# AFGHL40T65SPD

## ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
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### DIODE CHARACTERISTICS

Reverse Recovery Time	$T_J = 175^\circ\text{C}$ $I_F = 20\text{ A}, di_F/dt = 200\text{ A}/\mu\text{s}$	trr	–	214	–	ns
Reverse Recovery Charge		Qrr	–	776	–	$\mu\text{C}$
Reverse Recovery Energy		Erec	–	51	–	$\mu\text{J}$

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL PERFORMANCE CHARACTERISTICS

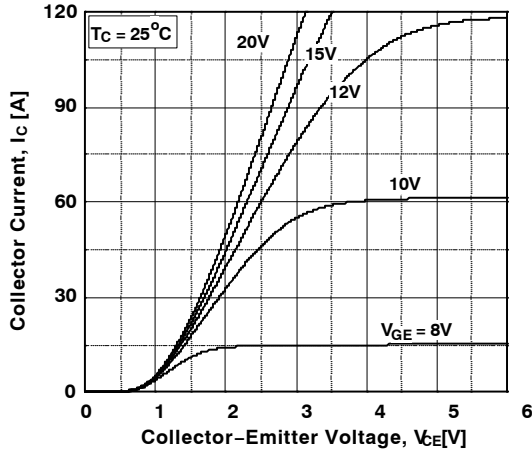


Figure 1. Typical Output Characteristics

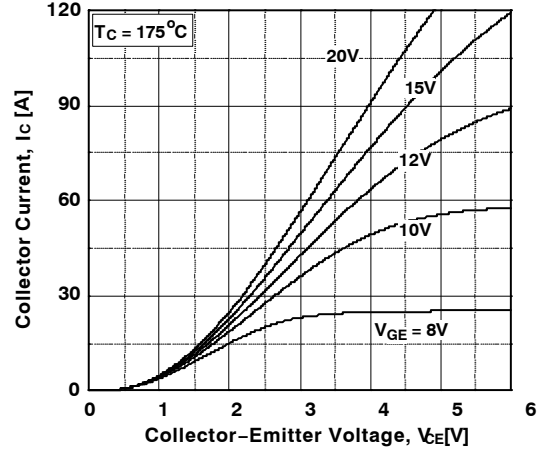


Figure 2. Typical Output Characteristics

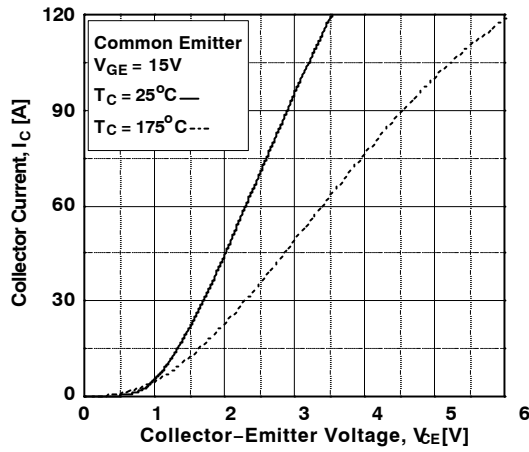


Figure 3. Typical Saturation Voltage Characteristics

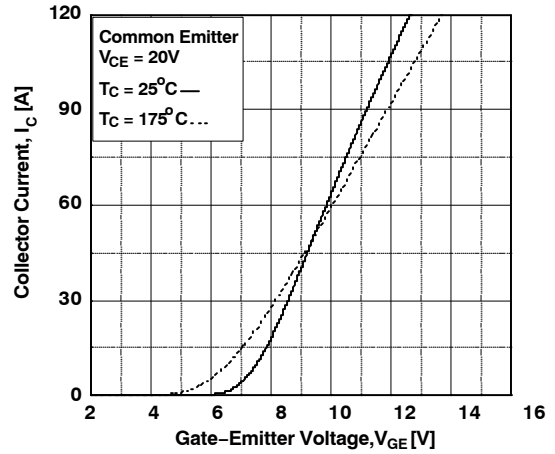


Figure 4. Transfer Characteristics

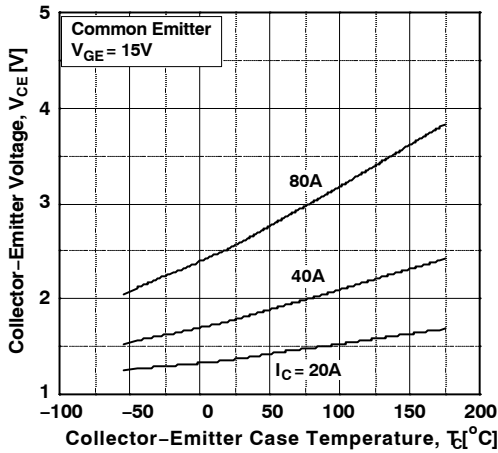


Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level

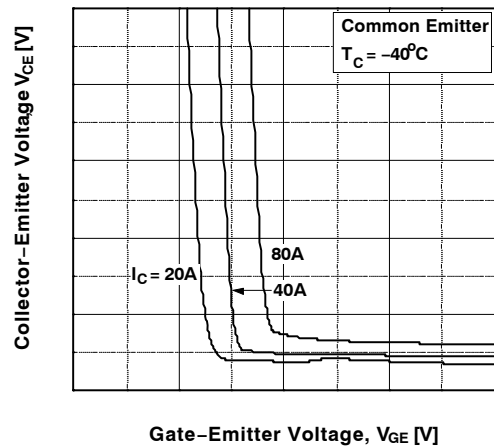


Figure 6. Saturation Voltage vs.  $V_{GE}$

TYPICAL PERFORMANCE CHARACTERISTICS

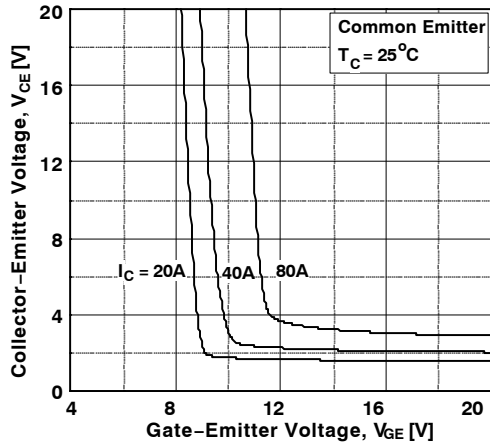


Figure 7. Saturation Voltage vs.  $V_{GE}$

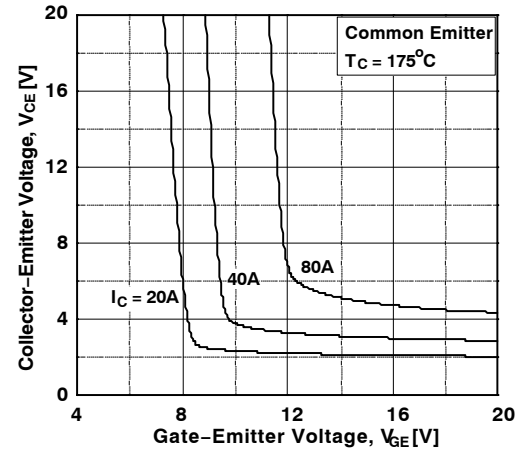


Figure 8. Saturation Voltage vs.  $V_{GE}$

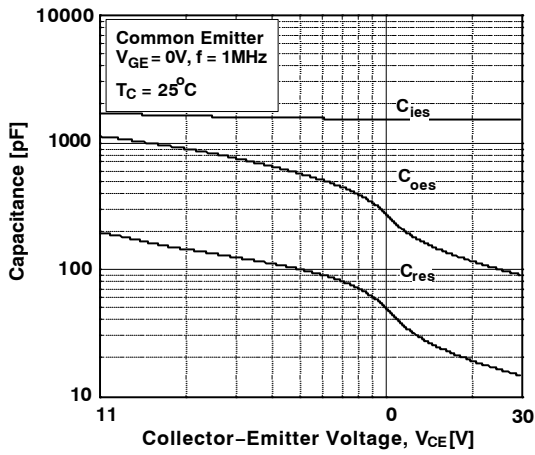


Figure 9. Capacitance Characteristics

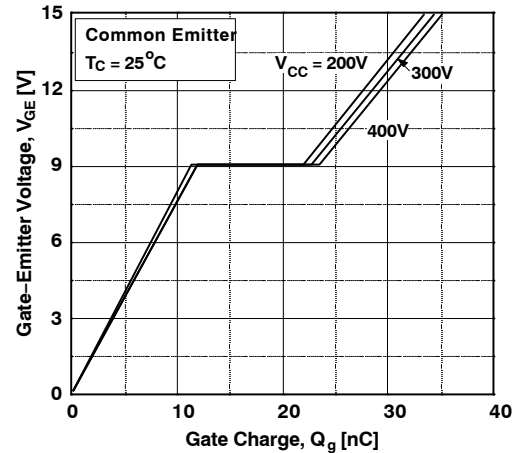


Figure 10. Gate charge Characteristics

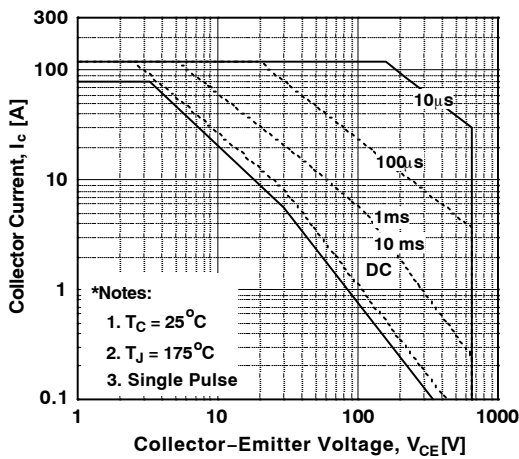


Figure 11. SOA Characteristics

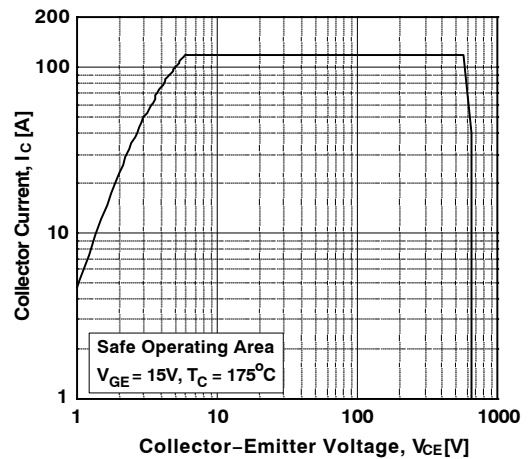


Figure 12. Turn off Switching SOA Characteristics

TYPICAL PERFORMANCE CHARACTERISTICS

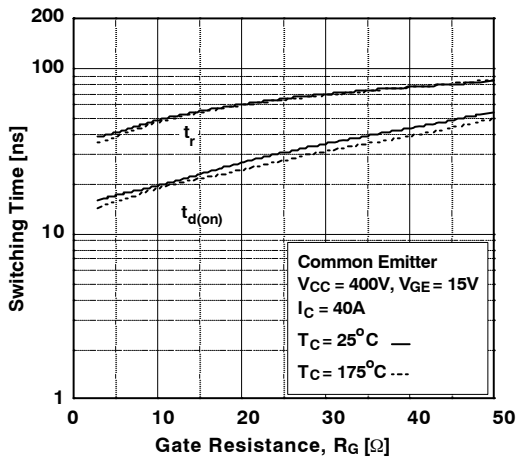


Figure 13. Turn-on Characteristics vs. Gate Resistance

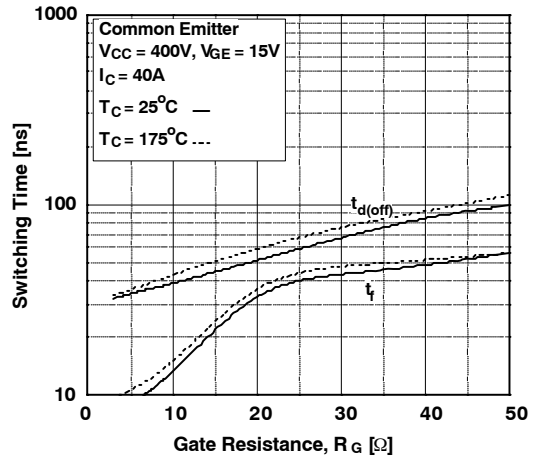


Figure 14. Turn-on Characteristics vs. Gate Resistance

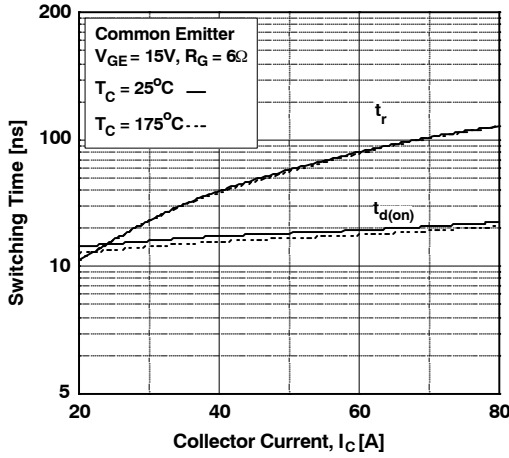


Figure 15. Turn-on Characteristics vs. Collector Current

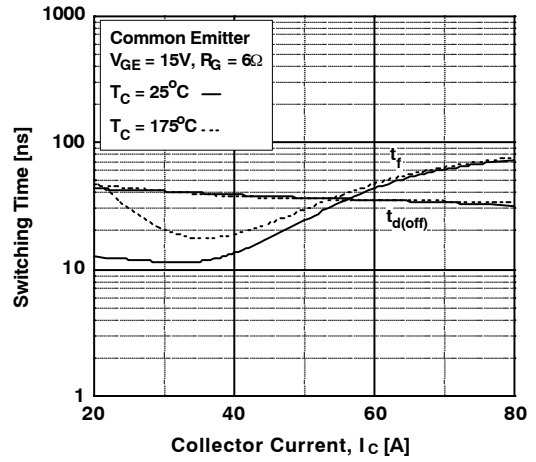


Figure 16. Turn-off Characteristics vs. Collector Current

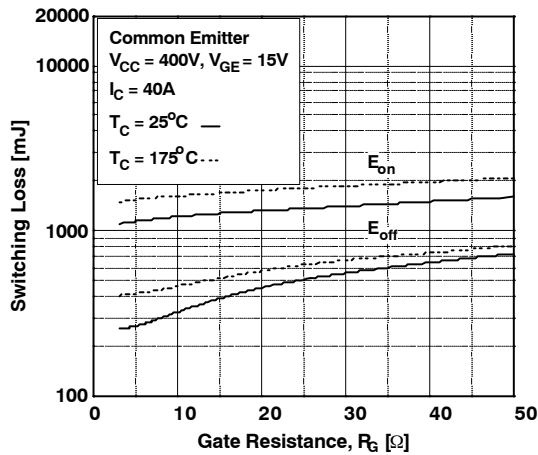


Figure 17. Switching Loss vs Gate Resistance

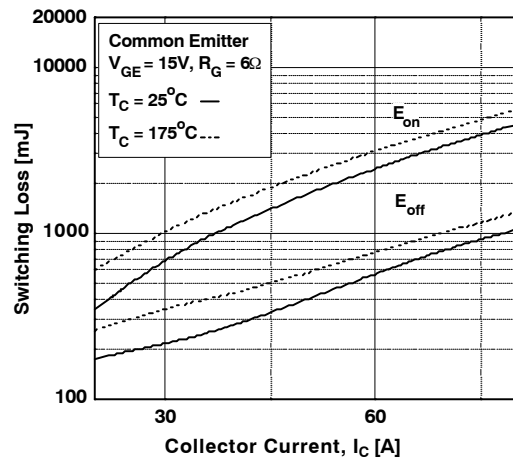


Figure 18. Switching Loss vs Collector Current

TYPICAL PERFORMANCE CHARACTERISTICS

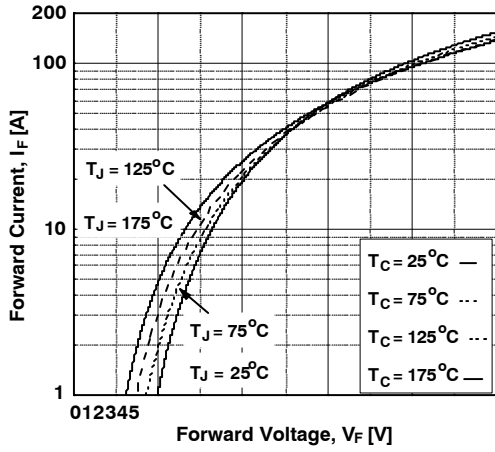


Figure 19. Forward Characteristics

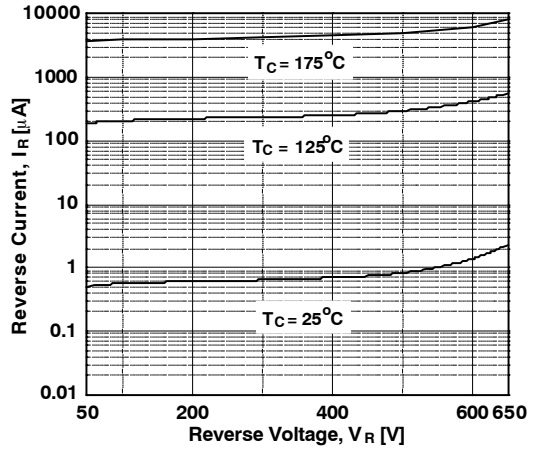


Figure 20. Reverse Current

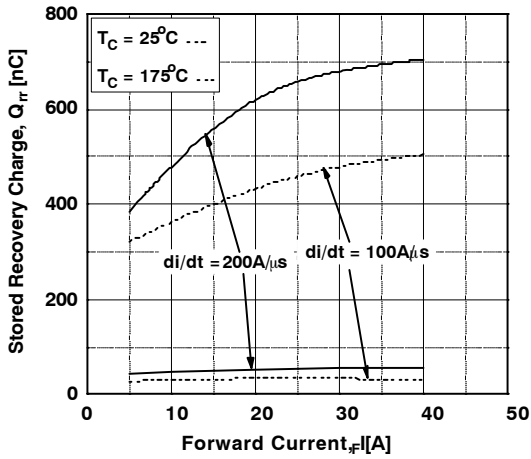


Figure 21. Stored Charge

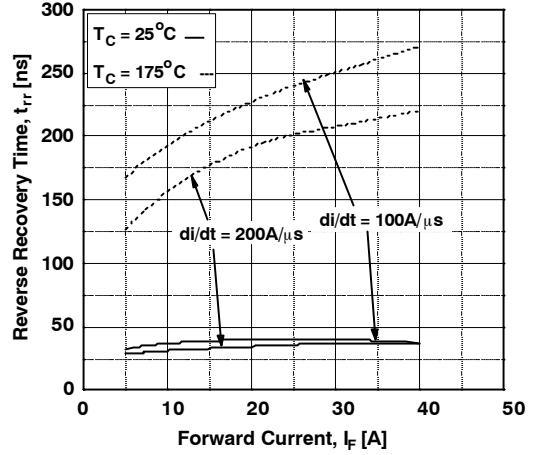


Figure 22. Reverse Recovery Time

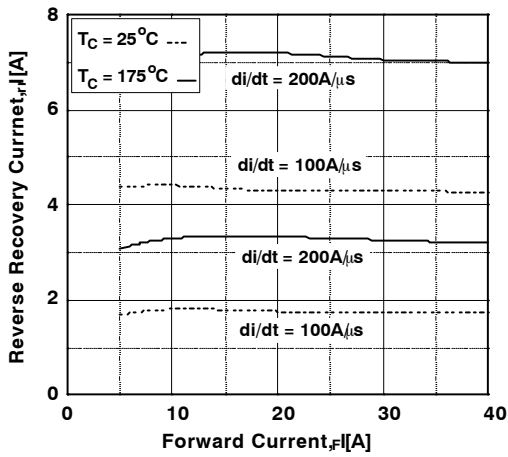


Figure 23. Reverse Recovery Current



# AFGHL40T65SPD

## TYPICAL PERFORMANCE CHARACTERISTICS

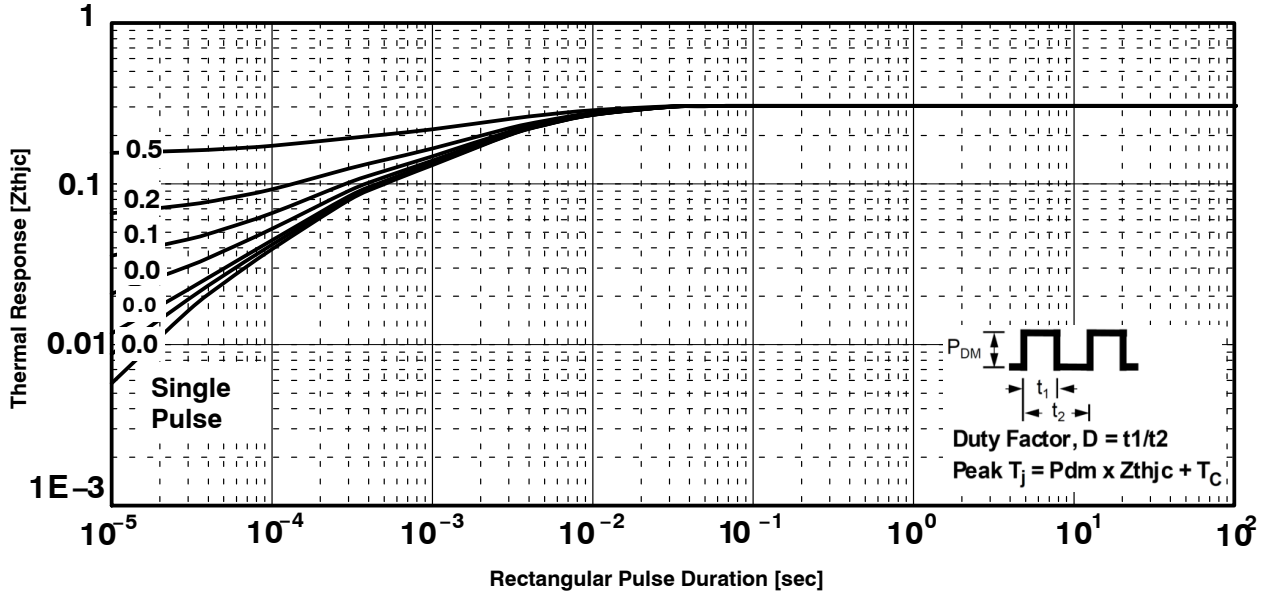


Figure 24. Transient Thermal Impedance of IGBT

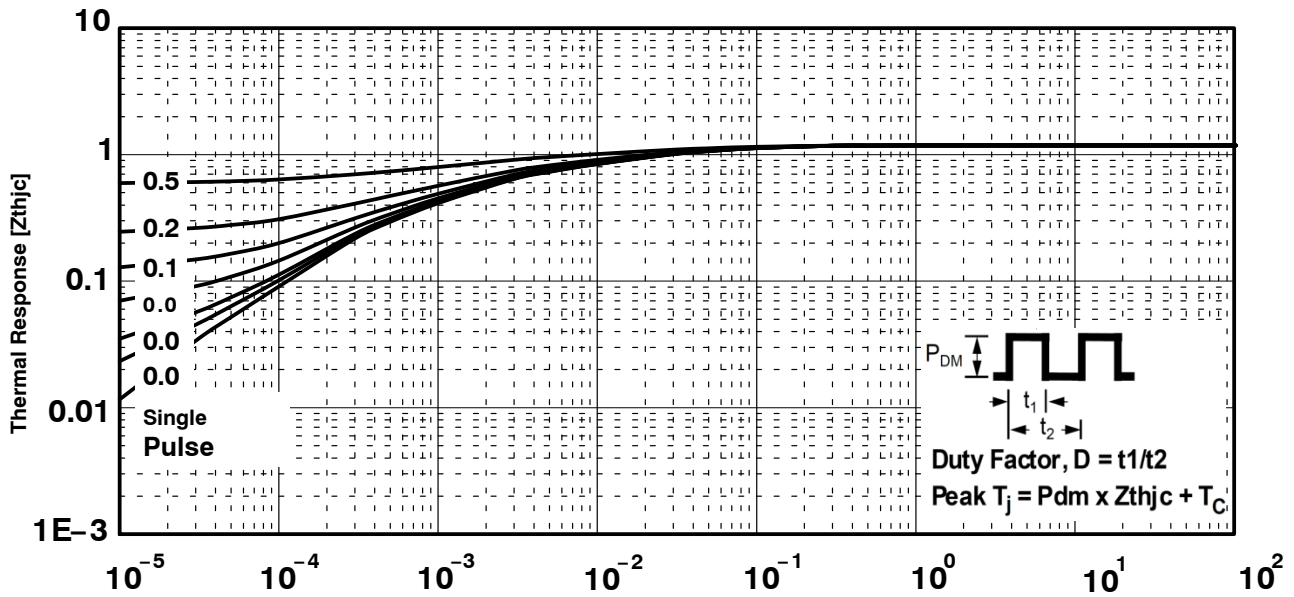
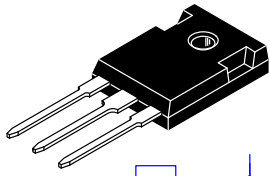


Figure 25. Transient Thermal Impedance of Diode

# MECHANICAL CASE OUTLINE

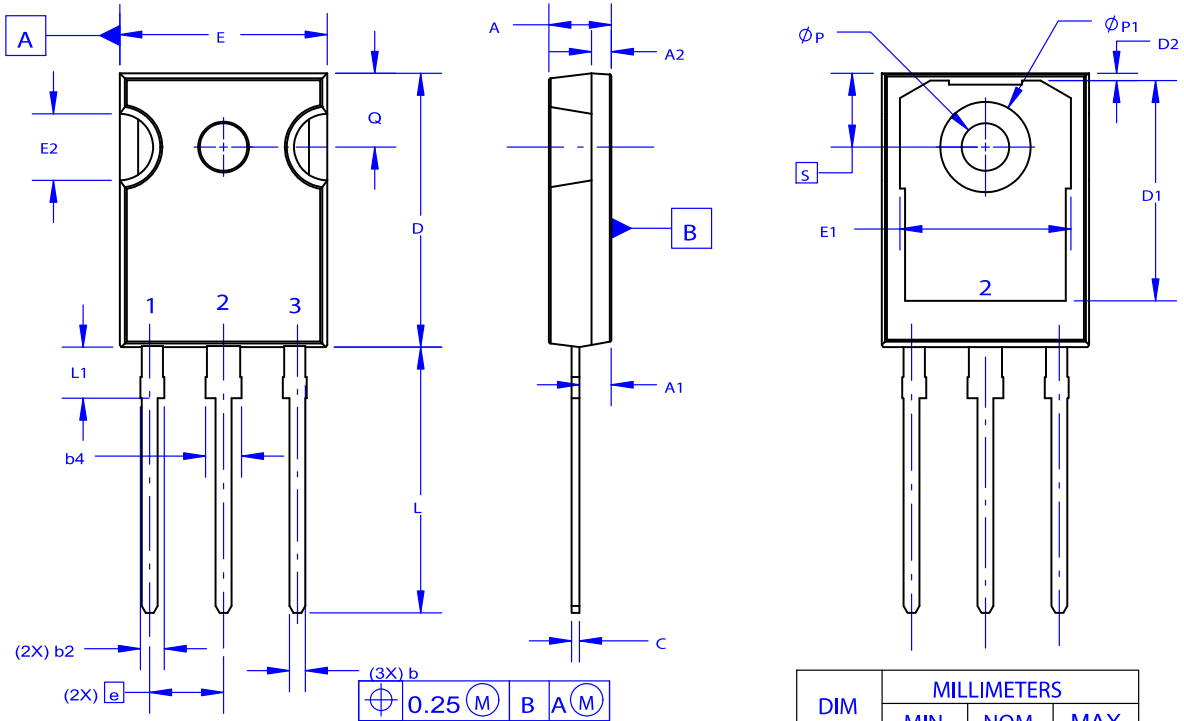
## PACKAGE DIMENSIONS

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TO-247-3LD  
CASE 340CX  
ISSUE O

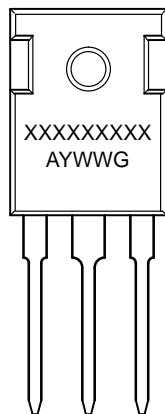
DATE 27 JUN 2018



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
- D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

### GENERIC MARKING DIAGRAM\*



- XXXXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- WW = Work Week
- G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.20	2.40	2.60
A2	1.40	1.50	1.60
D	20.32	20.57	20.82
E	15.37	15.62	15.87
E2	4.96	5.08	5.20
e	~	5.56	~
L	19.75	20.00	20.25
L1	3.69	3.81	3.93
ØP	3.51	3.58	3.65
Q	5.34	5.46	5.58
S	5.34	5.46	5.58
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
b4	2.42	2.54	2.66
c	0.51	0.61	0.71
D1	13.08	~	~
D2	0.51	0.93	1.35
E1	12.81	~	~
ØP1	6.60	6.80	7.00

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